

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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of

Attorney Docket Number

2269-4218US (99-0796.00/US)

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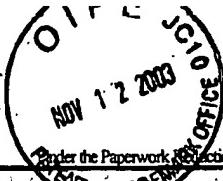
FOREIGN PATENT DOCUMENTS

Examiner Signature	HUNG VU	Date Considered	04/19/04
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PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

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<p>Substitute for form 1449A/PTO</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(use as many sheets as necessary)</p>		<i>Complete if Known</i>	
		Application Number	09/651,620
		Filing Date	August 30, 2000
		First Named Inventor	Eugene P. Marsh
		Group Art Unit	2811
		Examiner Name	H. Vu
Attorney Docket Number		2269-4218US (99-0796.00/US)	
Sheet	1	of	2

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
V		US-4,250,210	02/1981	Crosby et al.	
		US-4,982,309	01/1991	Shepherd	
		US-5,080,862	01/1992	Luthra	
		US-5,128,016	06/1992	Glenning et al.	
		US-5,130,172	07/1992	Hicks et al.	
		US-5,241,137	08/1993	Kiribayashi	
		US-5,288,875	02/1994	Chen et al.	
		US-5,314,727	05/1994	McCormick et al.	
		US-5,352,488	10/1994	Spencer et al.	
		US-5,525,181	06/1996	Bruckner et al.	
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		US-5,614,795	03/1997	Kim	
		US-5,618,761	04/1997	Eguchi et al.	
		US-5,662,815	09/1997	Kim	
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		US-5,729,054	03/1998	Summerfelt et al.	
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		US-5,994,034	11/1999	Maebara	
V		US-6,197,628 B1	03/2001	Vaatstra et al.	

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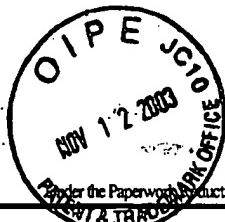
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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet

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of

Complete if Known

Application Number	09/651,620
Filing Date	August 30, 2000
First Named Inventor	Eugene P. Marsh
Group Art Unit	2811
Examiner Name	H. Vu

Attorney Docket Number 2269-42181US (99-0796.00/LIS)

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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
✓n		Cowles et al., Chemical Communications, p. 392, 1969.	
		Green et al., "Chemical Vapor Deposition of Ruthenium and Ruthenium Dioxide Films", J. Electrochem. Soc., Vol. 132, No. 11, pp. 2677-2685, Nov. 1985.	
		Simpson et al., "Atomic Layer Epitaxy," Chem Br., Vol. 23, No. 1, pp. 37-38, 40, Jan. 1987.	
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		Norton et al., "Organometallic Chemical Vapour Deposition of Platinum and Gold: Heterogeneous Deposition and Surface Chemistry," Surface Science, 307-309, pp. 172-176, 1994.	
		Borup et al., "Electrochemical and Vacuum Behavior of Carbon Monoxide and Lead Coadsorbed on Platinum (111)," J. Electroanalytical Chem., Vol. 374, pp. 235-244, 1994.	
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		Viljanen, "Monolayer Thickness in Atomic Layer Deposition," Thin Solid Films, Vol. 279, pp. 124-130, 1996.	
		George et al., "Surface Chemistry for Atomic Layer Growth," J. Phys. Chem., Vol. 100, pp. 13121-13131, 1996.	
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✓n		Min et al., "Atomic Layer Deposition of TiN Films by Alternate Supply of Tetrakis (ethylmethylamino)-Titanium and Ammonia," Jpn. J. Appl. Phys., Vol. 37, pp. 4999-5004, 1998.	

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